

Hisato Yabuta

List of Publications by Year in descending order

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38
papers

2,066
citations

471509

17
h-index

395702

33
g-index

38
all docs

38
docs citations

38
times ranked

1988
citing authors

#	ARTICLE	IF	CITATIONS
1	Structural investigation of ferroelectric BiFeO ₃ –BaTiO ₃ solid solutions near the rhombohedral–pseudocubic phase boundary. Applied Physics Letters, 2020, 116, .	3.3	5
2	Enhancement of tetragonal anisotropy and stabilisation of the tetragonal phase by Bi/Mn-double-doping in BaTiO ₃ ferroelectric ceramics. Scientific Reports, 2017, 7, 45842.	3.3	21
3	Microscopic structure and electrical transport property of sputter-deposited amorphous indium-gallium-zinc oxide semiconductor films. Journal of Physics: Conference Series, 2014, 518, 012001.	0.4	12
4	Platelet NaNbO ₃ grown by single-step molten salt synthesis: Study on bismuth migration in topochemical conversion reaction. Japanese Journal of Applied Physics, 2014, 53, 09PB08.	1.5	1
5	Characterizations of epitaxial Bi(Mg _{1/2} Ti _{1/2})O ₃ –Bi(Zn _{1/2} Ti _{1/2})O ₃ solid solution films grown by pulsed laser deposition. Japanese Journal of Applied Physics, 2014, 53, 05FE06.	2	2
6	Structure and Magnetic Properties of BiFe _{1-x} Co _x O ₃ and Bi _{0.9} Sm _{0.1} Fe _{1-x} Co _x O ₃ . Inorganic Chemistry, 2013, 52, 10698-10704.	4.0	24
7	Growth of (1-x)NaNbO ₃ –xBaTiO ₃ Single Crystals by Slow-Cooling and Flux Methods. Japanese Journal of Applied Physics, 2013, 52, 09KC02.	1.5	2
8	Microstructure and Piezoelectric Properties of BaTiO ₃ -Bi(Mg _{1/2} Ti _{1/2})O ₃ -BiFeO ₃ Ceramics. Key Engineering Materials, 2013, 566, 59-63.	0.4	2
9	Growth of (111) One-Axis-Oriented Bi(Mg _{1/2} Ti _{1/2})O ₃ Films on (100)Si Substrates. Japanese Journal of Applied Physics, 2013, 52, 04CH09.	1.5	4
10	Effect of sintering condition and V-doping on the piezoelectric properties of BaTiO ₃ –Bi(Mg _{1/2} Ti _{1/2})O ₃ –BiFeO ₃ ceramics. Journal of the Ceramic Society of Japan, 2013, 121, 589-592.	1.5	13
11	Film Thickness Dependence of Ferroelectric Properties of (111)-Oriented Epitaxial Bi(Mg _{1/2} Ti _{1/2})O ₃ Films. Japanese Journal of Applied Physics, 2012, 51, 09LA04.	1.5	13
12	Sequential Phase Transitions in Sm Substituted BiFeO ₃ . Funtai Oyobi Fummtsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2012, 59, 239-245.	0.2	0
13	Piezoelectric enhancement of relaxor-based lead-free piezoelectric ceramics by nanodomain engineering. , 2012, , .		0
14	Microstructure of BaTiO ₃ –Bi(Mg _{1/2} Ti _{1/2})O ₃ –BiFeO ₃ Piezoelectric Ceramics. Japanese Journal of Applied Physics, 2012, 51, 09LD04.		20
15	Microstructure of BaTiO ₃ –Bi(Mg _{1/2} Ti _{1/2})O ₃ –BiFeO ₃ Piezoelectric Ceramics. Japanese Journal of Applied Physics, 2012, 51, 09LD04.		34
16	Structural Transformation of Hexagonal (0001)BaTiO ₃ Ceramics to Tetragonal (111)BaTiO ₃ Ceramics. Japanese Journal of Applied Physics, 2011, 50, 09ND01.	1.5	22
17	Structural, Dielectric, and Piezoelectric Properties of Mn-Doped BaTiO ₃ –Bi(Mg _{1/2} Ti _{1/2})O ₃ –BiFeO ₃ Ceramics. Japanese Journal of Applied Physics, 2011, 50, 09ND07.	1.5	42
18	Sequential Phase Transitions in Sm Substituted BiFeO ₃ . Japanese Journal of Applied Physics, 2011, 50, 09NE08.	1.5	23

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19	Structural, Dielectric, and Piezoelectric Properties of Mn-Doped BaTiO ₃ Bi(Mg _{1/2} Ti _{1/2})O ₃ BiFeO ₃ Ceramics1.5 Japanese Journal of Applied Physics, 2011, 50, 09ND07.		42
20	Sequential Phase Transitions in Sm Substituted BiFeO ₃ . Japanese Journal of Applied Physics, 2011, 50, 09NE08.	1.5	10
21	Electronic states of magnetic refrigerator materials Mn _{0.9} Fe _{1.1} P _{0.55} As _{0.45} using soft x-ray magnetic circular dichroism. Journal of Physics: Conference Series, 2010, 200, 012199.	0.4	1
22	Sputtering formation of p-type SnO thin-film transistors on glass toward oxide complimentary circuits. Applied Physics Letters, 2010, 97, .	3.3	189
23	Materials, Devices, and Circuits of Transparent Amorphous-Oxide Semiconductor. Journal of Display Technology, 2009, 5, 531-540.	1.2	71
24	42.1: <i>Invited Paper</i>: Improved Amorphous InGaZnO TFTs. Digest of Technical Papers SID International Symposium, 2008, 39, 621-624.	0.3	56
25	Circuits using uniform TFTs based on amorphous InGaZnO. Journal of the Society for Information Display, 2007, 15, 915-921.	2.1	121
26	Neutron powder diffraction study of the site disorder in. Journal of Magnetism and Magnetic Materials, 2007, 310, 380-382.	2.3	1
27	Pressure effects on the first order transition in MnFe(P,As) and MnFe(P,Ge). Journal of Magnetism and Magnetic Materials, 2007, 310, 1826-1828.	2.3	11
28	High-mobility thin-film transistor with amorphous InGaZnO ₄ channel fabricated by room temperature rf-magnetron sputtering. Applied Physics Letters, 2006, 89, 112123.	3.3	1,048
29	Temperature- and Field-Induced First-Order Ferromagnetic Transitions in MnFe(P _{1-x} Gex). Journal of the Physical Society of Japan, 2006, 75, 113707.	1.6	21
30	NMR study of YbInNi ₄ . Journal of Magnetism and Magnetic Materials, 2004, 272-276, 205-206.	2.3	0
31	Low Temperature Recovery of Ru/(Ba, Sr)TiO ₃ /Ru Capacitors Degraded by Forming Gas Annealing. Japanese Journal of Applied Physics, 2000, 39, 2063-2067.	1.5	10
32	Electrical Properties of (Ba, Sr)TiO ₃ Films on Ru Bottom Electrodes Prepared by Electron Cyclotron Resonance Plasma Chemical Vapor Deposition at Extremely Low Temperature and Rapid Thermal Annealing. Japanese Journal of Applied Physics, 1999, 38, 2200-2204.	1.5	14
33	Plasma CVD of (BaSr)TiO ₃ Dielectrics for Gigabit DRAM Capacitors. , 1999, 3, 123-133.		8
34	A stacked capacitor technology with ECR plasma MOCVD (Ba,Sr)TiO ₃ and RuO ₂ /Ru/TiN/TiSi _x storage nodes for Gb-scale DRAMs. IEEE Transactions on Electron Devices, 1997, 44, 1076-1083.	3.0	46
35	Low Temperature Deposition of (Ba,Sr)TiO ₃ Films by Electron Cyclotron Resonance Plasma Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1996, 35, 5089-5093.	1.5	28
36	(Ba+Sr)/Ti ratio dependence of the dielectric properties for (Ba _{0.5} Sr _{0.5})TiO ₃ thin films prepared by ion beam sputtering. Applied Physics Letters, 1994, 64, 1644-1646.	3.3	125

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37	Magnetic and NMR study of valence phase transition in $\text{Yb}_{1-x}\text{TxCu}_4$ (T = Ag and Au). Journal of Magnetism and Magnetic Materials, 1992, 104-107, 653-654.	2.3	7
38	Relaxor Characteristics of $\text{BaTiO}_3\text{-Bi}(\text{Mg}_{1/2}\text{Ti}_{1/2})\text{O}_3$ Ceramics. Key Engineering Materials, 0, 485, 31-34.	0.4	18